



DMT5015LFDF

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
50V	15mΩ @ V <sub>GS</sub> = 10V	9.1A
500	$23m\Omega @ V_{GS} = 4.5V$	7.4A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch
- Adaptor Switch
- Notebook PC

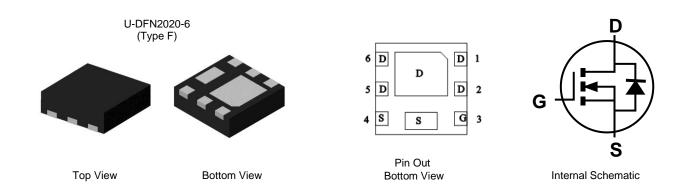
#### 50V N-CHANNEL ENHANCEMENT MODE MOSFET

#### Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.007 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity per Reel
DMT5015LFDF-7	T5	7	3,000
DMT5015LFDF-13	T5	13	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



T5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

#### Date Code Key

Notes:

Year	201	6	2017		2018	20	19	2020		2021	2	022
Code	D		E		F	(	3	Н				J
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Month	Juli	100	Intal		inay	Juli	Jui	Aug	Ocp	001	1101	Dec



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V <sub>DSS</sub>	50	V	
Gate-Source Voltage		V <sub>GSS</sub>	±16	V	
	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	9.1 7.3	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	11.5 9.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%		IDM	60	А	
Continuous Source-Drain Diode Current	T <sub>A</sub> = +25°C	IS	2.2	А	
Avalanche Current (Note 7) L = 0.1mH		I <sub>AS</sub>	14.4	А	
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	10.4	mJ		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Dawar Dissinction (Nata 5)	T <sub>A</sub> = +25°C	P	0.82	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.52		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Р	153	°C/W	
Thermal Resistance, Junction to Amblent (Note 5)	t<10s	$R_{\theta JA}$	96	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P	1.97	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.2		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Peri	67	°C/W	
Thermal Resistance, Junction to Amblent (Note 6)	t<10s	R <sub>0JA</sub>	42		
Thermal Resistance, Junction to Case (Note 6)	Steady State	R <sub>θJC</sub>	14		
Operating and Storage Temperature Range		T <sub>J.</sub> T <sub>STG</sub>	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

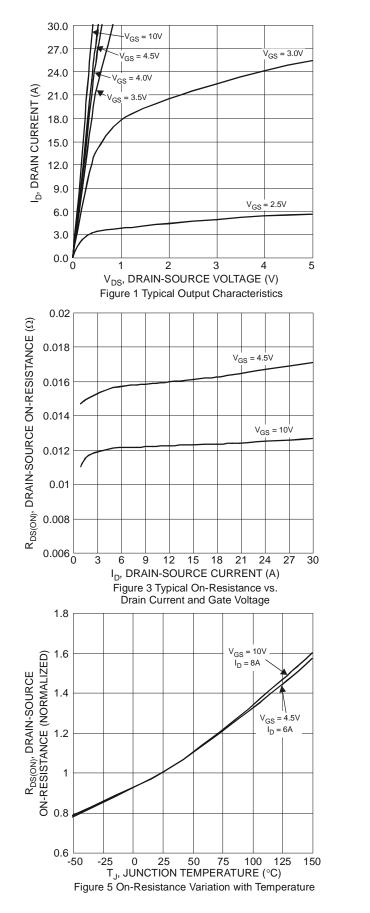
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Symbol	IVIIII	тур	IVIAA	Unit	Test condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>		_	1	μÂ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	1635			1100	10.0	VGS = ±100, VDS = 00	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5		2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			10.5	15	_	$V_{GS} = 10V, I_D = 8A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	14	23	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 5A$	
DYNAMIC CHARACTERISTICS (Note 9)	1		1				
Input Capacitance	CISS	_	902.7	—			
Output Capacitance	C <sub>OSS</sub>	_	301.4	—	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	—	15.2	-		1 = 1.000112	
Gate Resistance	R <sub>G</sub>	_	1.9	—	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	6.1	-			
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	_	14	—	nC	Vps = 25V. lp = 8A	
Gate-Source Charge	Q <sub>GS</sub>	_	2.4	-	nc	$v_{DS} = 25v, i_D = 6A$	
Gate-Drain Charge	Q <sub>GD</sub>		1.6	—			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.8	—			
Turn-On Rise Time	t <sub>R</sub>	_	5.1	—		$V_{DS} = 25V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		10.6	—	ns	$R_G = 3\Omega$ , $I_D = 8A$	
Turn-Off Fall Time	t <sub>F</sub>		2.7	—			
Reverse Recovery Time	t <sub>RR</sub>	_	18.9	_	ns	I <sub>F</sub> = 8A, di/dt = 100A/µs	
Reverse Recovery Charge	Q <sub>RR</sub>		9.2	—	nC	I <sub>F</sub> = 8A, di/dt = 100A/µs	

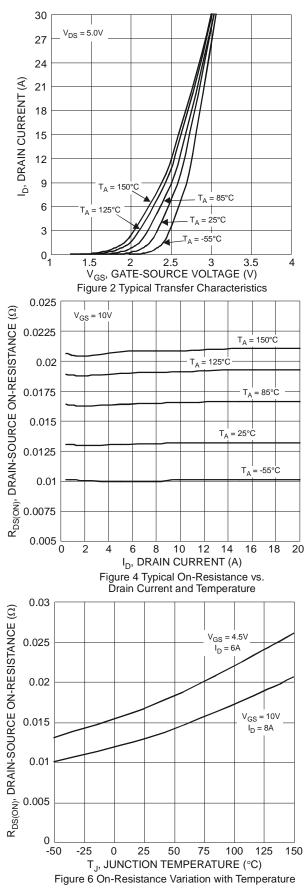
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. IAS and EAS rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.



# DMT5015LFDF







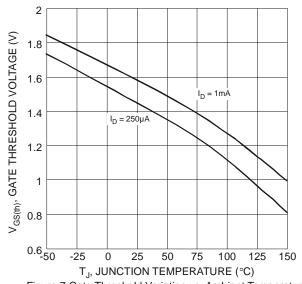


Figure 7 Gate Threshold Variation vs. Ambient Temperature

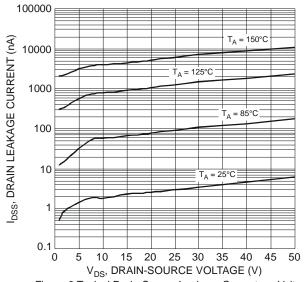
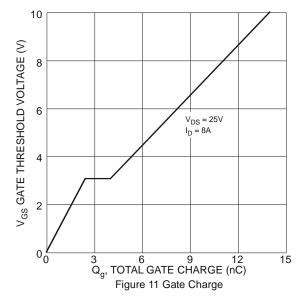
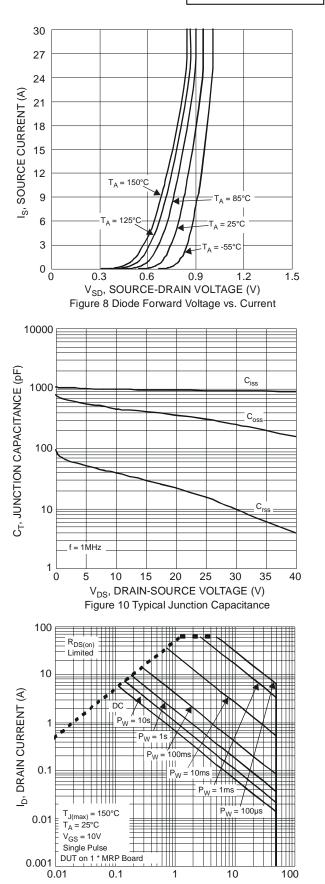


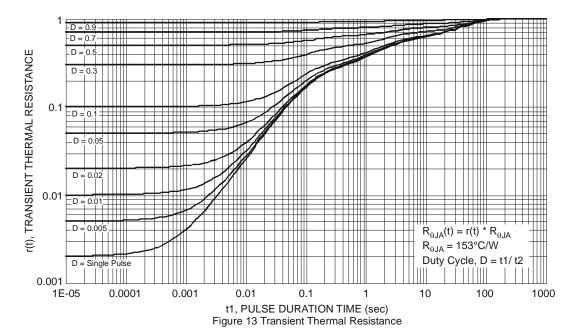
Figure 9 Typical Drain-Source Leakage Current vs. Voltage





V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area

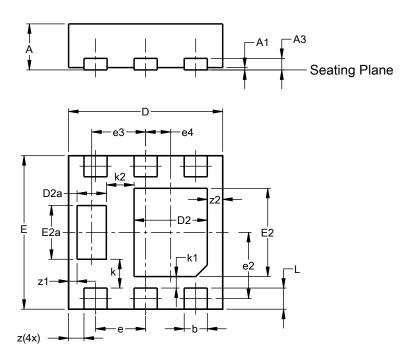






# **Package Outline Dimensions**

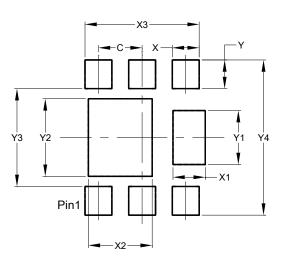
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 (Type F)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.03					
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
E	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
e3		0.70 BSC					
e4	-	0.325 BSC					
k		0.37 BS	С				
k1		0.15 BS					
k2		0.36 BS					
L	0.225	0.325	0.275				
z		0.20 BS					
z1		).110 BS					
z2		0.20 BS					
All C	Dimens	ions in	mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 (Type F)

Dimensions	Value (in mm)		
С	0.650		
Х	0.400		
X1	0.480		
X2	0.950		
X3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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